

# P2N222

## Amplifier NPN Silicon

### Features

- These are Pb-Free Devices

### MAXIMUM RATINGS (T<sub>A</sub>)

Characteristic				
Collector-Emitter Voltage				
Collector-Base Voltage				
Emitter-Base Voltage	V <sub>EB0</sub>	6.0	V <sub>dc</sub>	
Collector Current - Continuous	I <sub>C</sub>	600	mA <sub>dc</sub>	
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C		625	mW	mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C				
Operating and Storage Junction Temperature Range				

### THERMAL CHARACTERISTICS

Characteristic	
Thermal Resistance, Junction to Ambient	
Thermal Resistance, Junction to Case	R <sub>θc</sub>

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Maximum Recommended Operating Conditions is not implied. Extended exposure to stresses above the Maximum Recommended Operating Conditions may affect device reliability.



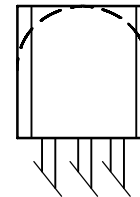
**onsemi**

onsemi.com

COLLECTOR



EMITTER



### ORDERING INFORMATION

Device	Package	Shipping†
P2N2222AG	TO-92 (Pb-Free)	5000 Units/Bulk
P2N2222ARL1G	TO-92 (Pb-Free)	2000/Tape & Ammo

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# P2N2222A

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	40	-	Vdc
Collector-Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	75	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	-	Vdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 3.0\text{ Vdc}$ )	$I_{CEX}$	-	10	nAdc
Collector Cutoff Current ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	-	0.01 10	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	10	nAdc
Collector Cutoff Current ( $V_{CE} = 10\text{ V}$ )	$I_{CEO}$	-	10	nAdc
Base Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 3.0\text{ Vdc}$ )	$I_{BEX}$	-	20	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 0.1\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $T_A = -55^\circ\text{C}$ ) ( $I_C = 150\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ ) (Note 1) ( $I_C = 150\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) (Note 1) ( $I_C = 500\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ ) (Note 1)	$h_{FE}$	35 50 75 35 100 50 40	- - - - 300 - -	-
Collector-Emitter Saturation Voltage (Note 1) ( $I_C = 150\text{ mAdc}$ , $I_B = 15\text{ mAdc}$ ) ( $I_C = 500\text{ mAdc}$ , $I_B = 50\text{ mAdc}$ )	$V_{CE(sat)}$	- -	0.3 1.0	Vdc
Base-Emitter Saturation Voltage (Note 1) ( $I_C = 150\text{ mAdc}$ , $I_B = 15\text{ mAdc}$ ) ( $I_C = 500\text{ mAdc}$ , $I_B = 50\text{ mAdc}$ )	$V_{BE(sat)}$	0.6 -	1.2 2.0	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Current-Gain - Bandwidth Product (Note 2) ( $I_C = 20\text{ mAdc}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )C	$f_T$	300	-	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	-	8.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	-	25	pF
Input Impedance ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	2.0 0.25	8.0 1.25	k $\Omega$
Voltage Feedback Ratio ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	- -	8.0 4.0	$\times 10^{-4}$
Small-Signal Current Gain ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	50 75	300 375	-
Output Admittance ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	5.0 25	35 200	$\mu\text{Mhos}$
Collector Base Time Constant ( $I_E = 20\text{ mAdc}$ , $V_{CB} = 20\text{ Vdc}$ , $f = 31.8\text{ MHz}$ )	$rb'C_c$	-	150	ps
Noise Figure ( $I_C = 100\text{ }\mu\text{Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	$N_F$	-	4.0	dB

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .
2.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

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## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>SWITCHING CHARACTERISTICS</b>				
Delay Time	$t_d$	-	10	ns
Rise Time				
Storage Time	$t_s$	-	225	ns
Fall Time				
	$t_f$	-	60	ns

### SWITCHING TIME EQUIVALENT TEST CIRCUITS

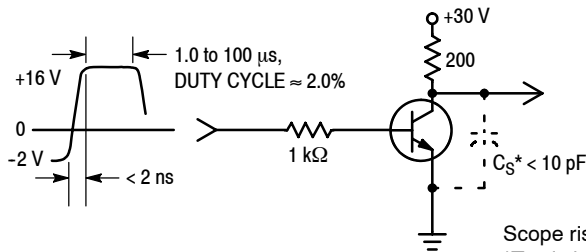


Figure 1. Turn-On Time

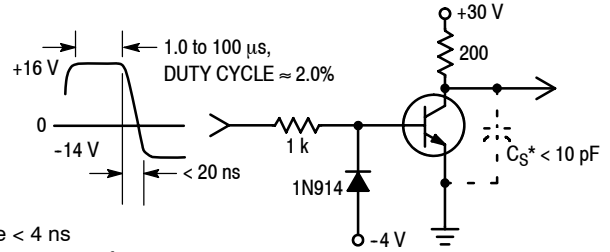


Figure 2. Turn-Off Time

Scope rise time < 4 ns  
\*Total shunt capacitance of test jig, connectors, and oscilloscope.

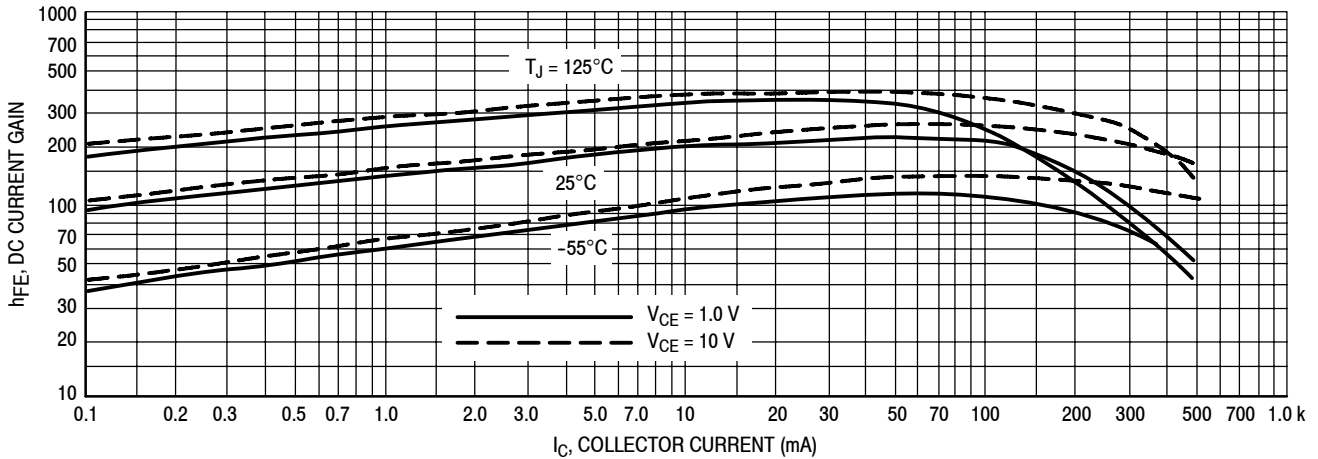


Figure 3. DC Current Gain

# P2N2222A

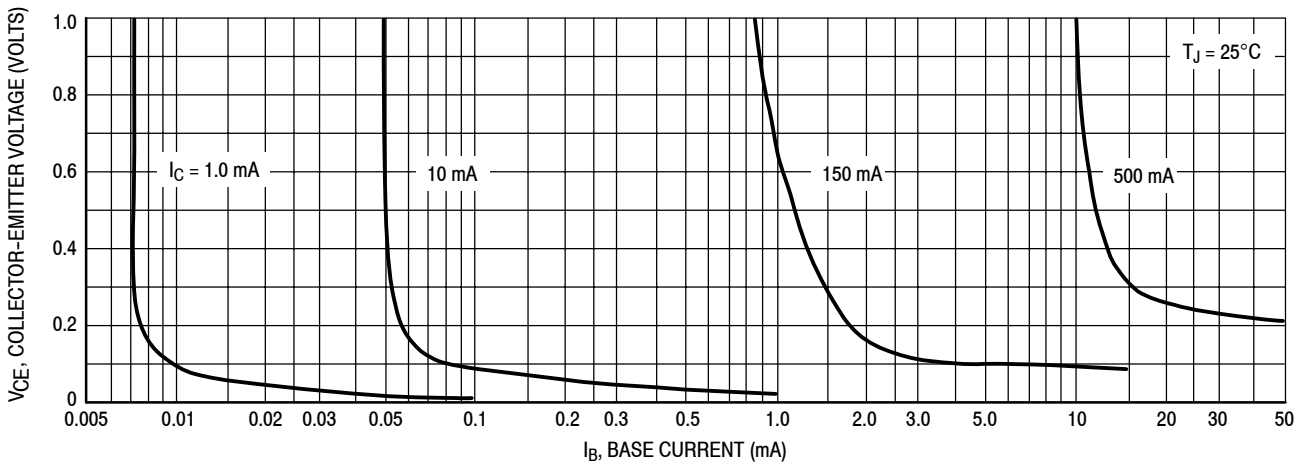


Figure 4. Collector Saturation Region

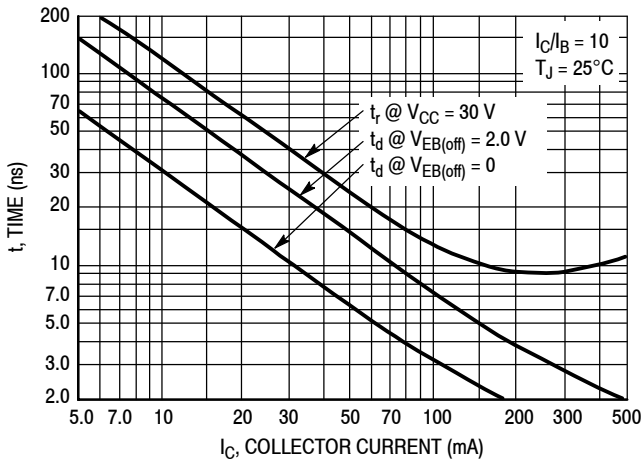


Figure 5. Turn-On Time

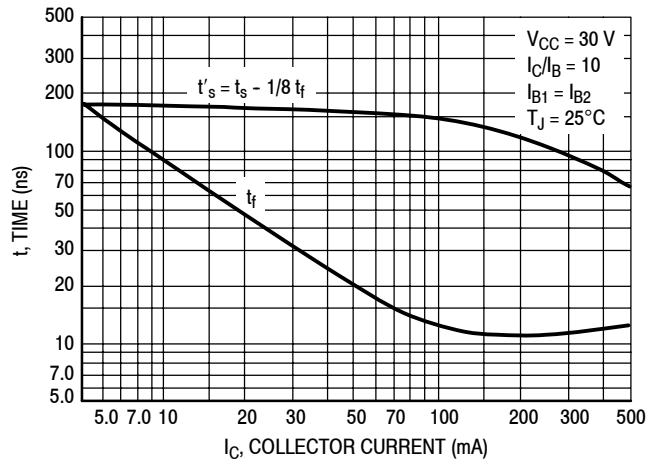


Figure 6. Turn-Off Time

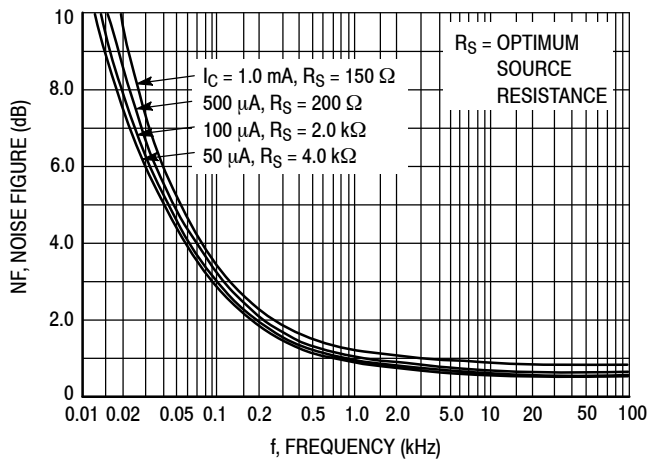


Figure 7. Frequency Effects

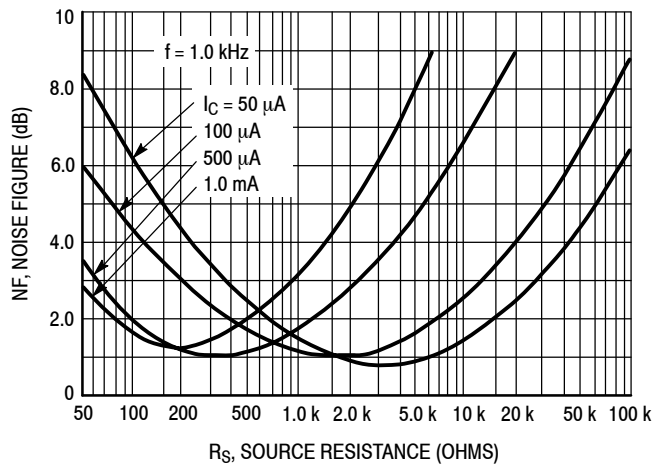


Figure 8. Source Resistance Effects

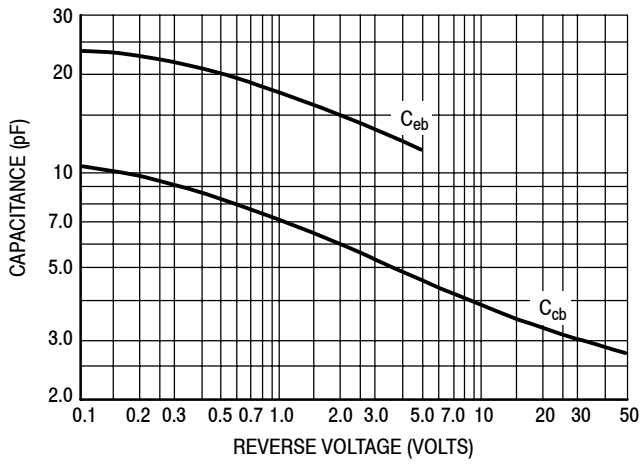


Figure 9. Capacitances

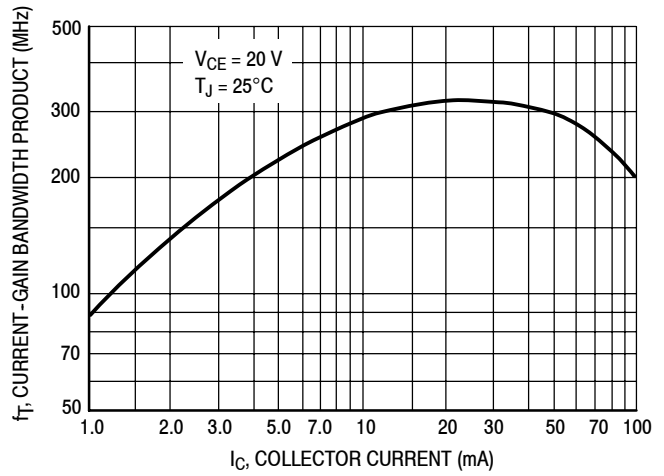


Figure 10. Current-Gain Bandwidth Product

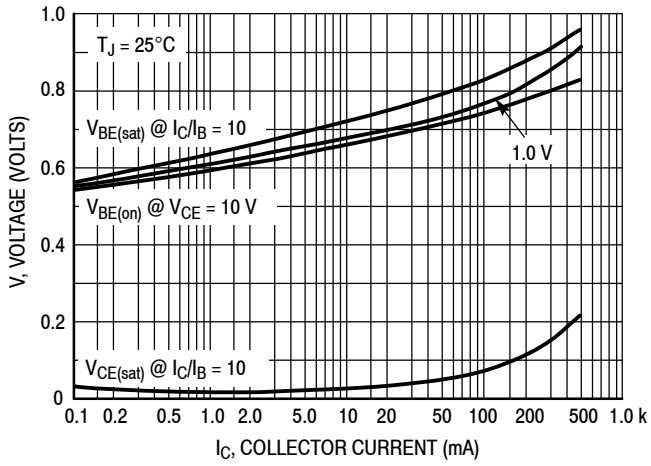


Figure 11. "On" Voltages

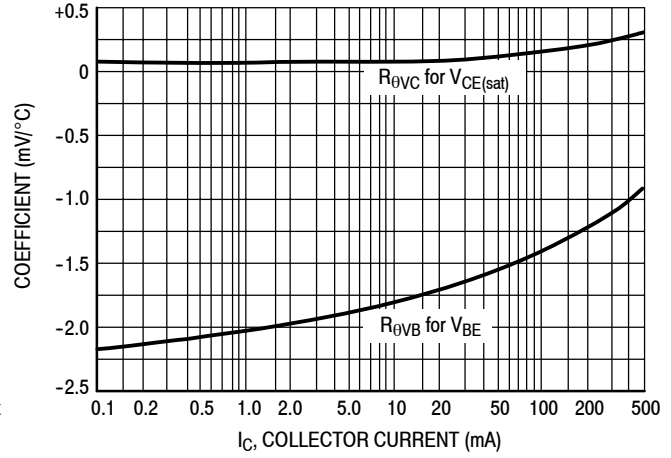
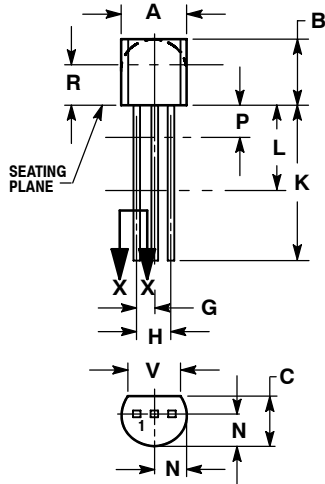


Figure 12. Temperature Coefficients

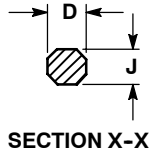
# P2N2222A

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AM



STRAIGHT LEAD  
BULK PACK

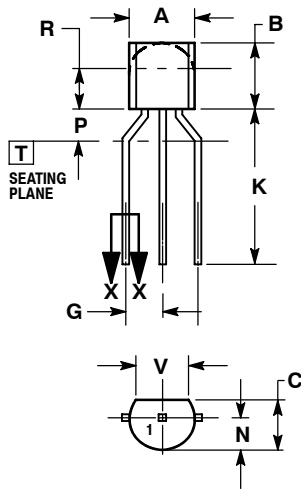


SECTION X-X

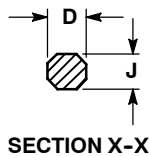
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 17:

1. COLLECTOR
2. BASE
3. EMITTER

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